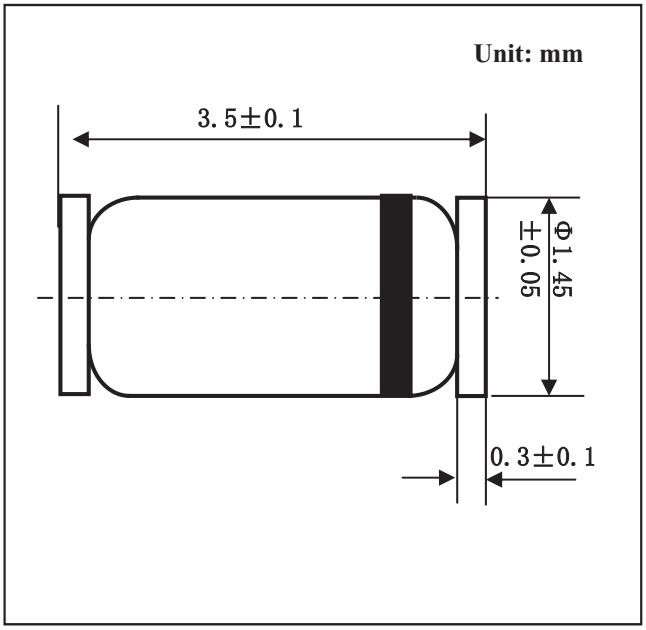
LL34 Schottky Barrier Diodes

Features

* Silicon Epitaxial Planner Diode
* Low Reverse Current and Low Forward Voltage
* Low Current Rectification and High Speed Switching
* High Reliability
* Used in Recorder, Radio, TV, Telephone as Detectors

Mechanical Data

* Case : MINI-MELF Glass Case (SOD-80)
* Polarity: Color Band Denotescathode Band
* Weight : Approx 0.05 gram



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Characteristic	Symbol	LL60	LL60P	Unit
Pepetitive Peak Reverse Voltage	V_{RRM}	40	45	V
Non-Repetitive Peak Forward Surge Current @t=1S	I_{FSM}	150	500	mA
Forward Continuous Current, T_A =25℃	I_F	30	50	m A
Operating and Strorage Temperature Range	T_J , T_{STG}	-65 to +125		℃

Characteristic		Symbol	Min	Tpy	Max	Unit
Forward Voltage						
I_F=1 mA	LL60	V_F	-	0.32	0.5	V
	LL60P		-	0.24	0.5	
I_F=30 mA	LL60		-	0.65	1.0	
I_F=200 mA	LL60P		-	0.65	1.0	
Rverse Current						
V_R=15V	LL60	I_R	-	0.1	0.5	uA
	LL60P		-	0.5	1.0	
Junction Capacitance						
V_R=1V, f=1MHz	LL60	Cj	-	2.0	-	PF
V_R=10V, f=1MHz	LL60P		-	6.0	-	
Reverse Recovery Time I_F=I_R=1mA , I_{rr}=1 mA, R_C=100Ω		Trr	-	-	1.0	nS

RATINGS AND CHARACTERISTIC CURVES

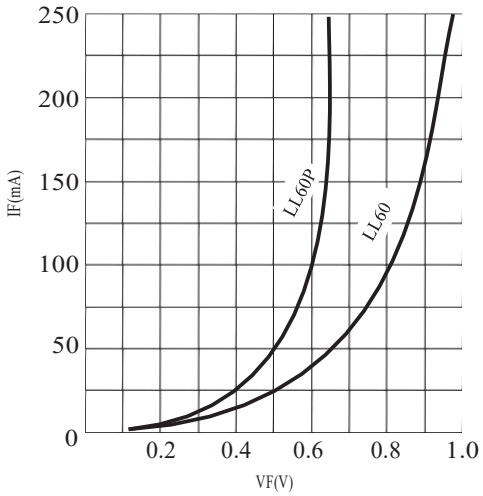


FIG.1 Fowrad Current vs. Forward Voltage

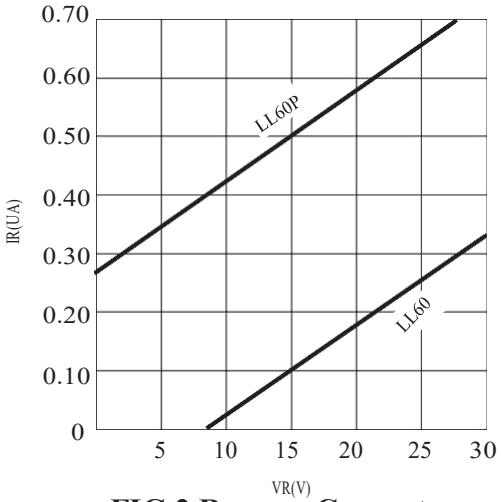


FIG.2 Reverse Current vs. Continuous Reverse Votlage

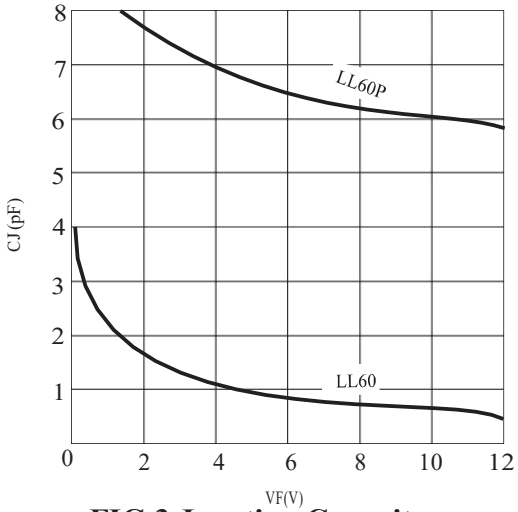


FIG.3 Junction Capacitance vs. Continuous Reverse Applied Voltage